

HM6288 Series

16384-word X 4-bit High Speed CMOS Static RAM

The Hitachi HM6288 is a high speed 64k static RAM organized as 16-kword x 4-bit. It realizes high speed access time (25/35/45 ns) and low power consumption, employing CMOS process technology.

It is most advantageous for the field where high speed and high density memory is required, such as the cache memory for main frame or 32-bit MPU.

The HM6288, packaged in a 300 mil plastic DIP and SOJ, is available for high density mounting. Low power version retains the data with battery back up.

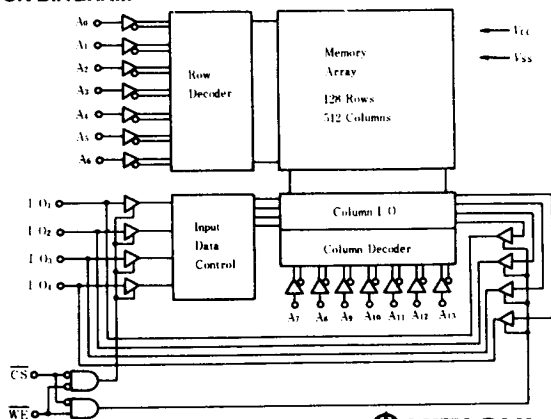
FEATURES

- Single 5V Supply and High Density Plastic Package.
- High Speed: Fast Access Time 25/35/45 ns (max.)
- Low Power dissipation
 - Active mode 300mW (typ.)
 - Standby mode 100μW (typ.)
- Completely Static Memory
 - No Clock or Timing Strobe Required.
- Equal Access and Cycle Times.
- Directly TTL Compatible – All Inputs and Outputs.

ORDERING INFORMATION

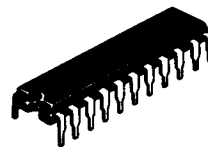
Type No.	Access Time	Package
HM6288P-25	25ns	300 mil 22-pin Plastic DIP (DP-22NB)
HM6288P-35	35ns	
HM6288LP-25	25ns	
HM6288LP-35	35ns	
HM6288JP-25	25ns	300 mil 24-pin SOJ (CP-24D)
HM6288JP-35	35ns	
HM6288LJP-25	25ns	
HM6288LJP-35	35ns	

BLOCK DIAGRAM



Hitachi America, Ltd. • Hitachi Plaza • 2000 Sierra Point Pkwy. • Brisbane, CA 94005-1819 • (415) 589-8300

59



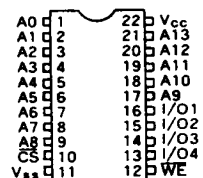
(DP-22NB)



(CP-24D)

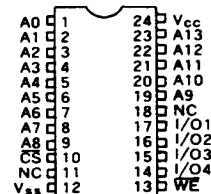
PIN ARRANGEMENT

HM6288P Series



(Top View)

HM6288JP Series



(Top View)

Pin Description

Pin Name	Function
A0 - A13	Address
I/O1 - I/O4	Input/Output
CS	Chip Select
WE	Write Enable
VCC	Power Supply
VSS	Ground

■ ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Rating	Unit
Voltage on Any Pin Relative to V_{SS}	V_T	-0.5^{*1} to $+7.0$	V
Power Dissipation	P_T	1.0	W
Operating Temperature	T_{op}	0 to $+70$	°C
Storage Temperature	T_{stg}	-55 to $+125$	°C
Temperature under Bias	T_{bias}	-10 to $+85$	°C

Note: *1. V_T min. = -2.0 V for pulse width ≤ 10 ns

■ TRUTH TABLE

$\overline{CS}$	$\overline{WE}$	Mode	V_{CC} Current	I/O Pin	Ref. Cycle
H	X	Standby	I_{SB}, I_{SB1}	High Z	
L	H	Read	I_{CC}	Dout	Read Cycle 1, 2
L	L	Write	I_{CC}	Din	Write Cycle 1, 2

■ RECOMMENDED DC OPERATING CONDITIONS ($T_a=0$ to $+70^\circ\text{C}$)

Parameter	Symbol	min	typ	max	Unit
Supply Voltage	V_{CC}	4.5	5.0	5.5	V
	V_{SS}	0	0	0	V
Input High (logic 1) Voltage	V_{IH}	2.2	—	6.0	V
Input Low (logic 0) Voltage	V_{IL}	-0.5^{*1}	—	0.8	V

Note: *1. V_{IL} min. = -2.0 V for pulse width ≤ 10 ns■ DC AND OPERATING CHARACTERISTICS ($T_a=0$ to $+70^\circ\text{C}$, $V_{CC}=5\text{V} \pm 10\%$, $V_{SS}=0\text{V}$)

Parameter	Symbol	Test Condition	min	typ*1	max	Unit
Input Leakage Current	$ I_{LI} $	$V_{CC} = \text{MAX.}$ $V_{IN} = V_{SS}$ to V_{CC}	—	—	2.0	μA
Output Leakage Current	$ I_{LO} $	$\overline{CS} = V_{IH}, V_{I/O} = V_{SS}$ to V_{CC}	—	—	2.0	μA
Operating Power Supply Current	I_{CC}	$\overline{CS} = V_{IL}, I_{I/O} = 0\text{mA}$, min. cycle	—	60	120	mA
Standby V_{CC} Current	I_{SB}	$\overline{CS} = V_{IH}$, min. cycle	—	15	30	mA
Standby V_{CC} Current 1	I_{SB1}^{*2}	$\overline{CS} \geq V_{CC} - 0.2\text{V}$	—	0.02	2.0	mA
	I_{SB1}^{*3}	$0\text{V} \leq V_{IN} \leq 0.2\text{V}$ or $V_{CC} - 0.2\text{V} \leq V_{IN}$	—	0.02	0.1	mA
Output Low Voltage	V_{OL}	$I_{OL} = 8\text{mA}$	—	—	0.4	V
Output High Voltage	V_{OH}	$I_{OH} = -4.0\text{mA}$	2.4	—	—	V

Notes: *1. Typical limits are at $V_{CC} = 5.0\text{V}$, $T_a = +25^\circ\text{C}$ and specified loading.

*2. P version

*3. LP version

■ CAPACITANCE ($T_a=25^\circ\text{C}$, $f=1.0\text{MHz}$)

Parameter	Symbol	Test Conditions	min	max	Unit
Input Capacitance	C_{in}	$V_{in} = 0\text{V}$	—	6	pF
Input/Output Capacitance	$C_{I/O}$	$V_{I/O} = 0\text{V}$	—	8	pF

Note: This parameter is sampled and not 100% tested



■ AC CHARACTERISTICS

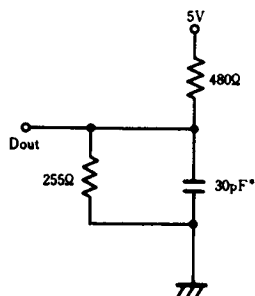
● AC Test Conditions

Input pulse levels: 0V to 3.0V

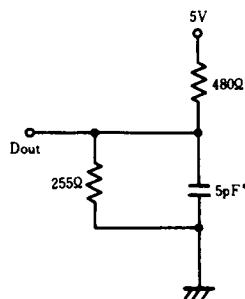
Input rise and fall times: 5ns

Input and Output timing reference levels: 1.5V

Output load: See Figure



*Including scope & jig.

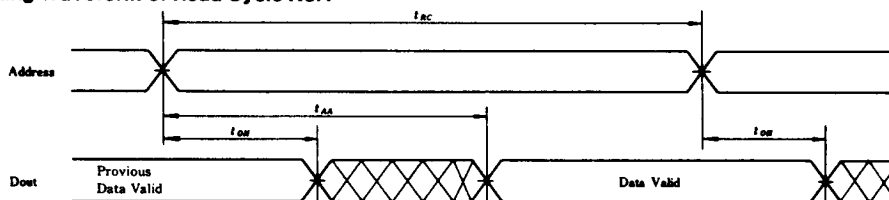
(for t_{HZ} , t_{LZ} , t_{WZ} & t_{OW})

■ READ CYCLE

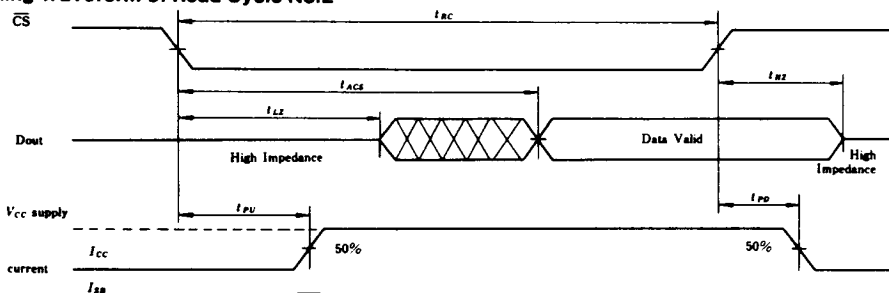
Parameter	Symbol	HM6288-25		HM6288-35		Unit
		min	max	min	max	
Read Cycle Time	t_{RC}	25	—	35	—	ns
Address Access Time	t_{AA}	—	25	—	35	ns
Chip Select Access Time	t_{ACS}	—	25	—	35	ns
Output Hold from Address Change	t_{OH}	3	—	5	—	ns
Chip Selection to Output in Low Z	t_{LZ}^*	5	—	5	—	ns
Chip Deselection to Output in High Z	t_{HZ}^*	0	12	0	20	ns
Chip Selection to Power Up Time	t_{PU}	0	—	0	—	ns
Chip Deselection to Power Down Time	t_{PD}	—	25	—	30	ns

* Transition is measured ± 200 mV from steady state voltage with Load(B).
This parameter is sampled and not 100% tested.

● Timing Waveform of Read Cycle No.1 [1] [2]



● Timing Waveform of Read Cycle No.2 [1] [3]



Notes: 1. $\overline{WE}$ is High for Read Cycle.
2. Device is continuously selected, $\overline{CS} = V_{IL}$.
3. Address Valid prior to or coincident with $\overline{CS}$ transition Low.



Hitachi America, Ltd. • Hitachi Plaza • 2000 Sierra Point Pkwy. • Brisbane, CA 94005-1819 • (415) 589-8300

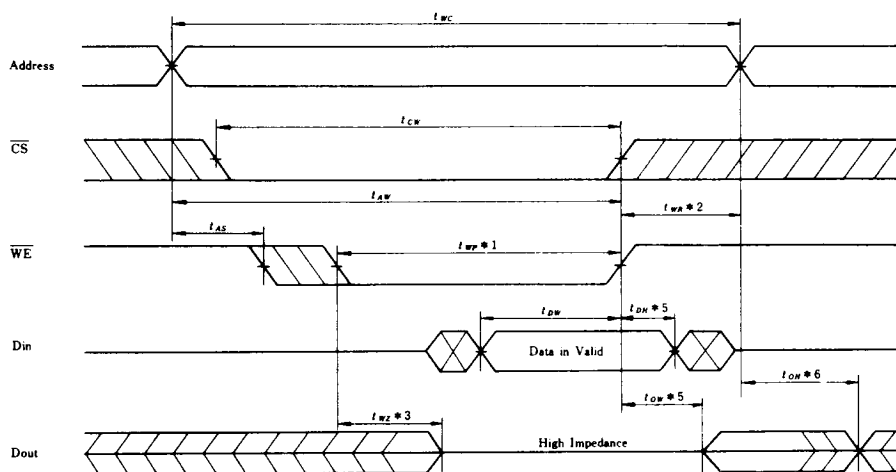
61

■ WRITE CYCLE

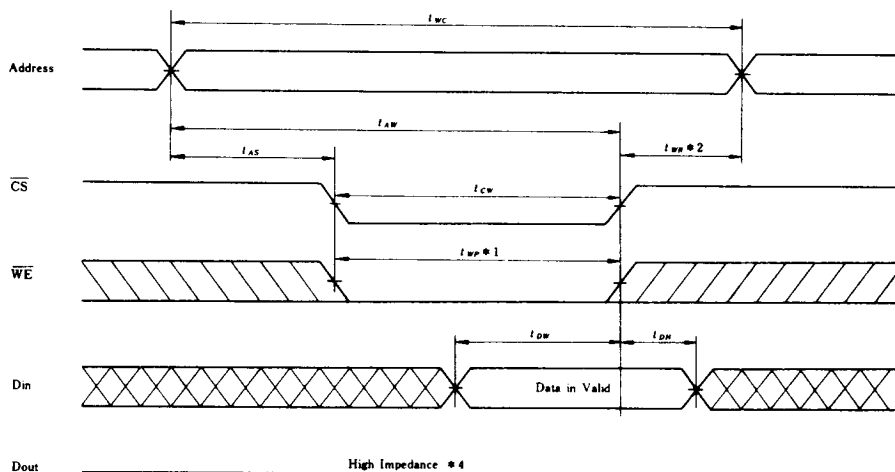
Parameter	Symbol	HM6288-25		HM6288-35		Unit
		min	max	min	max	
Write Cycle Time	t_{WC}	25	—	35	—	ns
Chip Selection to End of Write	t_{CW}	20	—	30	—	ns
Address Valid to End of Write	t_{AW}	20	—	30	—	ns
Address Setup Time	t_{AS}	0	—	0	—	ns
Write Pulse Width	t_{WP}	20	—	30	—	ns
Write Recovery Time	t_{WR}	0	—	0	—	ns
Data Valid to End of Write	t_{DW}	12	—	20	—	ns
Data Hold Time	t_{DH}	0	—	0	—	ns
Write Enabled to Output in High Z	t_{WZ}^*	0	8	0	10	ns
Output Active from End of Write	t_{OW}^*	5	—	5	—	ns

- * Transition is measured $\pm 200\text{mV}$ from steady state voltage with Load (B).
This parameter is sampled and not 100% tested.

● Timing Waveform of Write Cycle No.1 (WE Controlled)



● Timing Waveform of Write Cycle No.2 (CS Controlled)



● Low V_{CC} Data Retention Characteristics ($T_a = 0$ to $+70^\circ\text{C}$)

(This Characteristics is guaranteed only for L-version.)

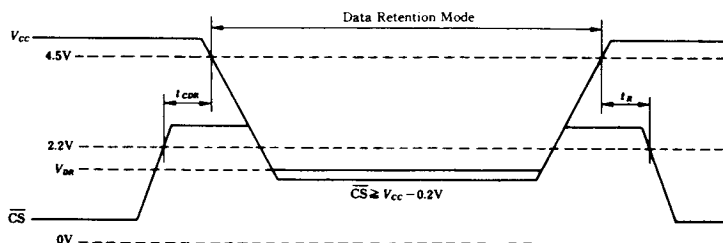
Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
V_{CC} for data retention	V_{DR}	2.0	—	—	V	$\overline{CS} \geq V_{CC} - 0.2\text{V}$
Data retention current	I_{CCDR}	—	—	50 ²⁾ 35 ³⁾	μA	$V_{in} \geq V_{CC} - 0.2\text{V}$ or $0\text{V} \leq V_{in} \leq 0.2\text{V}$
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	See retention waveform
Operation recovery time	t_R	t_{RC} ¹⁾	—	—	ns	

NOTE: 1. t_{RC} = Read cycle time

2. $V_{CC} = 3.0\text{V}$

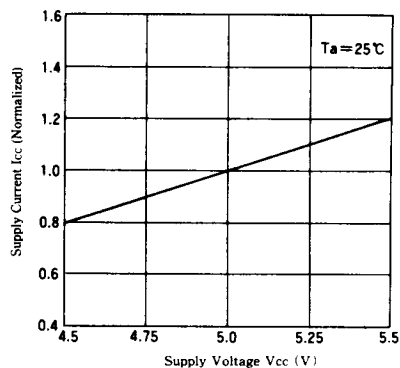
3. $V_{CC} = 2.0\text{V}$

Low V_{CC} Data Retention Waveform

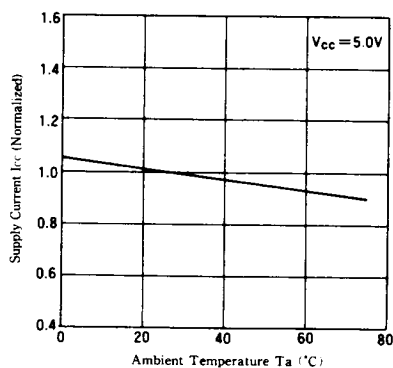


Hitachi America, Ltd. • Hitachi Plaza • 2000 Sierra Point Pkwy. • Brisbane, CA 94005-1819 • (415) 589-8300 63

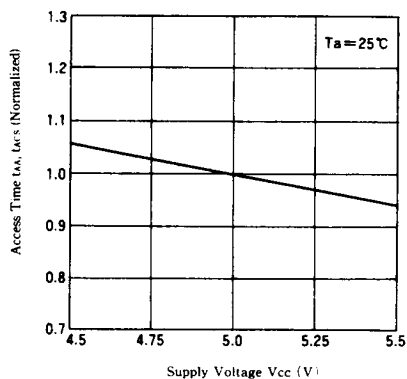
SUPPLY CURRENT VS. SUPPLY VOLTAGE



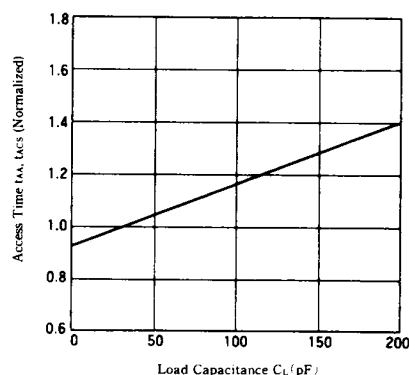
SUPPLY CURRENT VS. AMBIENT TEMPERATURE



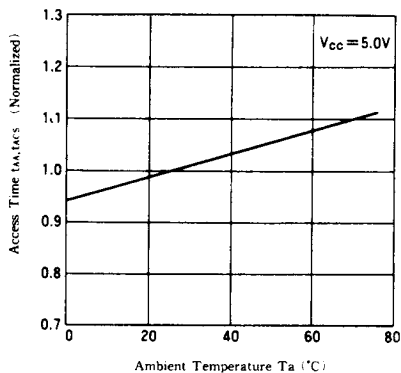
ACCESS TIME VS. SUPPLY VOLTAGE



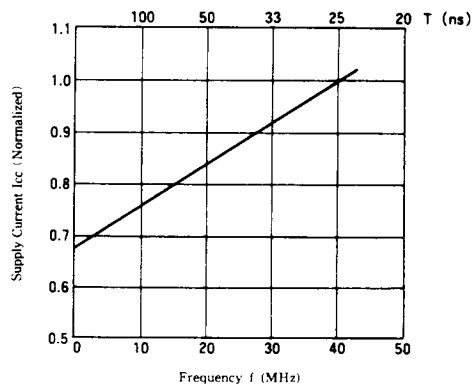
ACCESS TIME VS. LOAD CAPACITANCE

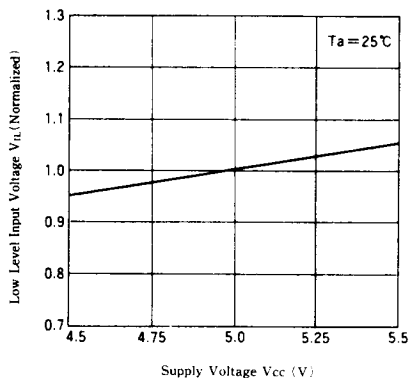
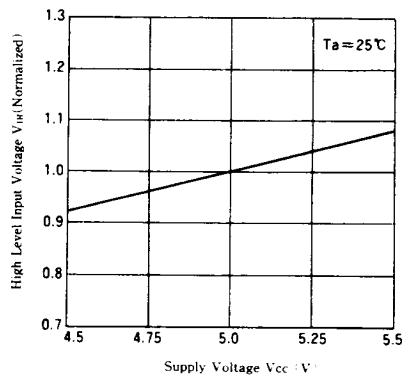


ACCESS TIME VS. AMBIENT TEMPERATURE

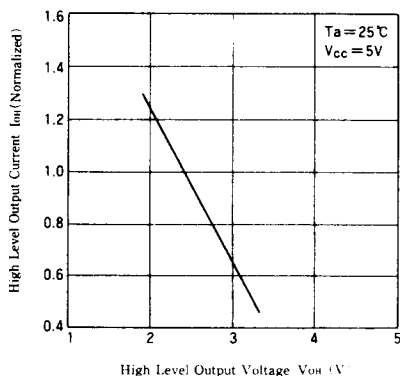


SUPPLY CURRENT VS. FREQUENCY

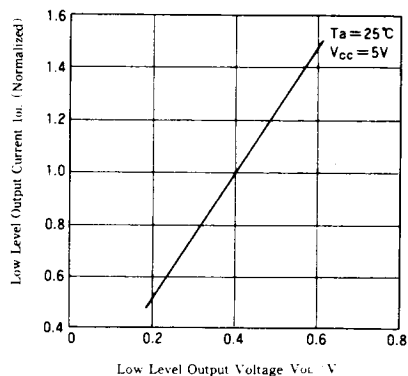


LOW LEVEL INPUT VOLTAGE VS.
SUPPLY VOLTAGEHIGH LEVEL INPUT VOLTAGE VS.
SUPPLY VOLTAGE

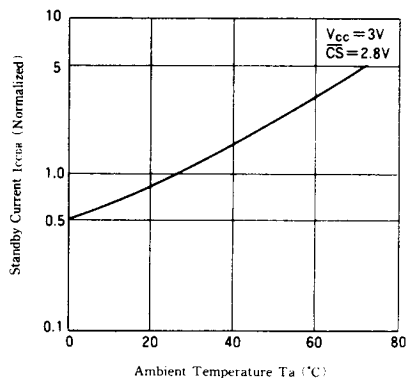
OUTPUT CURRENT VS. OUTPUT VOLTAGE(1)



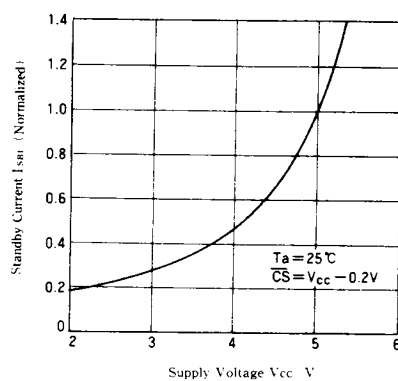
OUTPUT CURRENT VS. OUTPUT VOLTAGE(2)



STANDBY CURRENT VS. AMBIENT TEMPERATURE



STANDBY CURRENT VS. SUPPLY VOLTAGE



STANDBY CURRENT VS. INPUT VOLTAGE

